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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/586,953	07/25/2006	Makoto Iida	128832	3409
25944	7590	03/04/2011	EXAMINER	
OLIFF & BERRIDGE, PLC P.O. BOX 320850 ALEXANDRIA, VA 22320-4850				SONG, MATTHEW J
ART UNIT		PAPER NUMBER		
1714				
		NOTIFICATION DATE		DELIVERY MODE
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**Please find below and/or attached an Office communication concerning this application or proceeding.**

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

OfficeAction25944@oliff.com  
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<b>Office Action Summary</b>	<b>Application No.</b>	<b>Applicant(s)</b>	
	10/586,953	IIDA ET AL.	
	<b>Examiner</b>	<b>Art Unit</b>	
	MATTHEW J. SONG	1714	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

#### Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

#### Status

1) Responsive to communication(s) filed on 07 December 2010.

2a) This action is **FINAL**.                    2b) This action is non-final.

3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

#### Disposition of Claims

4) Claim(s) 49, 50, 55-74, 77, and 78 is/are pending in the application.

4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.

5) Claim(s) \_\_\_\_\_ is/are allowed.

6) Claim(s) 49,50,55-74,77 and 78 is/are rejected.

7) Claim(s) \_\_\_\_\_ is/are objected to.

8) Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

#### Application Papers

9) The specification is objected to by the Examiner.

10) The drawing(s) filed on \_\_\_\_\_ is/are: a) accepted or b) objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

#### Priority under 35 U.S.C. § 119

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

a) All    b) Some \* c) None of:  
 1. Certified copies of the priority documents have been received.  
 2. Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

#### Attachment(s)

1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)	4) <input type="checkbox"/> Interview Summary (PTO-413)
2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail Date. _____ .
3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO/SB/08)	5) <input type="checkbox"/> Notice of Informal Patent Application
Paper No(s)/Mail Date _____.	6) <input type="checkbox"/> Other: _____ .

## **DETAILED ACTION**

### **Claim Rejections - 35 USC § 112**

The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

Claim 49 and 77 is rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention.

Claim 49 claims the “components made of quartz are other than the crucible” in line 10. This is a negative limitation because it excludes the crucible, and there is no support in the original disclosure for the exclusion of the crucible. Any negative limitation or exclusionary proviso must have basis in the original disclosure and the mere absence of a positive recitation is not basis for an exclusion. (MPEP 2173.05(i). The same arguments apply to

### **Claim Rejections - 35 USC § 103**

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Claims 49-50 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sakurada et al (US 2003/0116082) in view of Takano et al (US 5,361,721), Ikeda et al (US 5,762,672) and Yokota et al (US 5,067,989).

Sakurada et al teaches a method for producing a silicon single crystal according to the Czochralski method comprising melting a raw material in a crucible (Abstract and [0059]); contacting a seed crystal on a melt surface ([0091]-[0097]); growing a silicon single crystal by using an apparatus ([0091]-[0097]). Sakurada et al teaches a defect region in the silicon single crystal contains Nv region outside an OSF ring over an entire region in a direction of a crystal growth axis (Fig 1).

Sakurada et al is silent to the Cu concentration of components made of quartz being 1 ppb or less and components made of quartz other than the crucible.

In a Czochralski crystal growth method, Takano et al teaches a Czochralski apparatus comprising a quartz crucible and a quartz ring shield (Abstract, Fig 1, col 5, ln 10-65 and col 6, ln 25-60), which clearly suggests a part made of quartz other than the crucible. Takano et al also

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teaches the quartz ring makes it possible to increase the growth rate of the single crystal (col 3, ln 60 to col 4, ln 40). Takano et al also teaches the quartz ring is made of high purity quartz glass and it is needless to say that the purity must be made as high as that of the quartz crucible so as to kept the melt as clean as possible (col 6, ln 50-60).

It would have been obvious to a person of ordinary skill in the art at the time of the invention to modify Sakurada et al by including a quartz ring, as taught by Takano et al, to increase the growth rate, thereby increasing productivity.

The combination of Sakurada et al and Takano et al teaches high purity quartz components within the Czochralski apparatus, thus is silent to the concentration of copper being 1 ppb or less.

In a method of making a quartz glass crucible for the Czochralski process, Ikeda et al teaches a quartz glass crucible with a impurity of 0.5 ppb or less of Cu (Abstract and Table 4), overlapping ranges are prima facie obvious. Ikeda et al teaches the high purity crucible allows for single crystal silicon to be obtain a plurality of times at a high crystallization ratio and enable high quality silicon single crystal (col 7, ln 45-55).

It would have been obvious to a person of ordinary skill in the art at the time of the invention to modify the combination of Sakurada et al and Takano et al by making the high purity quartz have an Cu concentration of 1 ppb or less, as taught by Ikeda et al, to reducing concentration of impurity, thereby forming a high purity silicon single crystal.

As to the temperature range of 1000°C or more is 1 ppb or less and a temperature less than 1000°C is 10 ppb or less, the crucible and quartz ring are present in the Czochralski apparatus during silicon single crystal growth, which requires heating to the melting point of

silicon, i.e. approximately 1400°C, thus is present at temperature greater than 1000°C and is also in the apparatus as the apparatus is heated to the melting point of silicon and cooled to room temperature from the melting point of silicon, thus is in a part where the temperature is less than 1000°C.

The combination of Sakurada et al, Takano et al and Ikeda et al is silent to the Cu concentration of the single crystal is less than  $1 \times 10^{12}$  atoms/cm<sup>3</sup>.

In a method of making silicon single crystal, Yokota et al teaches Cu contained as impurities in a single crystal silicon grown using the Czochralski method is at concentration of less than 0.1 ppta so that oxygen induced stacking faults are reduced to an absolute minimum (Abstract and col 3, ln 1-60). A concentration of less than 0.1 ppta overlaps the claimed range of  $1 \times 10^{12}$  atoms/cm<sup>3</sup> because the range of less than 0.1 ppta includes 0. Overlapping ranges are prima facie obvious (MPEP 2144.05).

It would have been obvious to a person of ordinary skill in the art at the time of the invention to modify the combination of Sakurada et al, Takano et al and Ikeda et al to have a Cu concentration of the single crystal less than  $1 \times 10^{12}$  atoms/cm<sup>3</sup> so that oxygen induced stacking faults are reduced to an absolute minimum, as taught by Yokota et al.

Referring to claim 50, the combination of Sakurada et al, Takano et al, Ikeda et al and Yokota et al does not teach any components formed with Cu as a raw material, and clearly suggests using high purity materials which do not include Cu as an impurity.

Claims 55-64, 74, and 78 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sakurada et al (US 2003/0116082) in view of Takano et al (US 5,361,721), Ikeda et al (US

5,762,672) and Yokota et al (US 5,067,989), as applied to claims 49-50 above, and further in view of Oda et al (US 2003/0000457).

The combination of Sakurada et al, Takano et al, Ikeda et al and Yokota et al teaches all of the limitations of claims 55-58, as discussed previously, except the taking out of furnace components and transferring in an environment of class 1000 or more, and cleaning which maintaining cleanliness at class 1000 or more.

In a pulling room apparatus for Czochralski growth, Oda et al teaches cleaning the furnace body and operations requiring high cleanliness are separated from each other (Abstract), and dismantling the furnace to cleaned ([0037]) and Oda et al teaches the degree of clean can be set to 1000, or 100 or 10 ([0040]-[0042]).

It would have been obvious to a person of ordinary skill in the art at the time of the invention to modify the combination of Sakurada et al, Takano et al, Ikeda et al and Yokota et al by transferring and cleaning in a high cleanliness environment, as taught by Oda et al, to safely perform operations which require cleanliness without any problems of contamination.

Referring to claim 59-62, the combination of Sakurada et al, Takano et al, Ikeda et al, Yokota et al and Oda et al does not teach any cleaning tools which contain Cu as raw material, and it would have been obvious to a person of ordinary skill in the art at the time of the invention to modify the combination of Sakurada et al, Takano et al, Ikeda et al, Yokota et al and Oda et al to not use cleaning tool which contain Cu as a raw material because the prior art recognizes Cu as an undesirable impurity.

Referring to claim 63-64, the combination of Sakurada et al, Takano et al, Ikeda et al, Yokota et al and Oda et al a cleanliness of 1000 or more.

Claims 65-73 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sakurada et al (US 2003/0116082) in view of Takano et al (US 5,361,721), Ikeda et al (US 5,762,672) and Yokota et al (US 5,067,989 and Oda et al (US 2003/0000457), as applied to claims 55-64 above, and further in view of Holder et al (US 6,344,083).

The combination of Sakurada et al, Takano et al, Ikeda et al, Yokota et al and Oda et al teaches all of the limitations of claim 65, as discussed above, except the time and energy parameters.

In a method of Czochralski crystal growth, Holder et al teaches melting an equilibrium phase of raw material for 3.5 hrs and utilization of heaters at appropriate temperature settings and insoluble (inert) gas (cols 1-6, lns 1-69).

It would have been obvious to a person of ordinary skill in the art at the time of the invention to modify the combination of Sakurada et al, Takano et al, Ikeda et al, Yokota et al and Oda et al with the teachings of Holder to ensure an appropriate and defect free fabrications of Si crystals.

As to the electrical power, this is a result effective variable readily determined by the operators usage. It would have been obvious to a person of ordinary skill in the art at the time of the invention to modify the combination of Sakurada et al, Takano et al, Ikeda et al, Yokota et al and Oda et al by using 80% or more of the power to melt the raw material more quickly, thereby increasing productivity.

Claim 77 is rejected under 35 U.S.C. 103(a) as being unpatentable over Sakurada et al (US 2003/0116082) in view of Takano et al (US 5,361,721), Ikeda et al (US 5,762,672) and Yokota et al (US 5,067,989), as applied to claims 49-50 above, and further in view of Tsuji et al (US 6,068,699).

The combination of Sakurada et al, Takano et al, Ikeda et al, and Yokota et al teaches all of the limitations of claim 77, as discussed above, except a quartz window with 10 ppb or less Cu.

In a Czochralski method, Tsuji et al teaches a quartz window **38** to observe the growth to measure diameter (Fig 4) and controlling diameter based on the measurements (col 1, ln 25-50).

It would have been obvious to a person of ordinary skill in the art at the time of the invention to modify the combination of Sakurada et al, Takano et al, Ikeda et al, Yokota et al by including a quartz window, as taught by Tsuji et al, to observe the crystal to thereby control diameter, thereby increasing uniformity.

As to the purity, the combination of Sakurada et al, Takano et al, Ikeda et al, Yokota et al as discussed above, teaches it is obvious to have the quartz parts be as high in purity as the crucible to reduce impurities and a concentration of less than 0.5 ppb is obvious.

### **Response to Arguments**

Applicant's arguments with respect to claims 49, 50, 55-74, 77, 78 have been considered but are moot in view of the new ground(s) of rejection.

### **Conclusion**

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to MATTHEW J. SONG whose telephone number is (571)272-1468. The examiner can normally be reached on M-F 11:00-7:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Kornakov can be reached on 571-272-1303. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

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